

IPA80R450P7XKSA1

IPA80R450P7XKSA1 Information



For Reference Only

Part Number IPA80R450P7XKSA1
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 800V 11A TO220

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPA80R450P7XKSA1 Specifications

Manufacturer Part NumberIPA80R450P7XKSA1ManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3 Full PackSeriesCoolMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C11A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 220μAGate Charge (Qg) (Max) @ Vgs24nC @ 10VInput Capacitance (Ciss) (Max) @ Vds770pF @ 500VVgs (Max)±20VFET FeatureSuper JunctionPower Dissipation (Max)29W (Tc)Rds On (Max) @ Id, Vgs450 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3FPackage / CaseTO-220-3 Full PackReport errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series CoolMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Parin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Super Junction Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case TO-220-3 Full Pack	Manufacturer Part Number	IPA80R450P7XKSA1
Package TO-220-3 Full Pack Series CoolMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 11A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 220μA Gate Charge (Qg) (Max) @ Vgs 24nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 770pF @ 500V Vgs (Max) ±20V FET Feature Super Junction Power Dissipation (Max) 29W (Tc) Rds On (Max) @ Id, Vgs 450 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Manufacturer	Infineon Technologies
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Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Super Junction Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package TO-220-3 Full Pack	Vgs(th) (Max) @ Id	3.5V @ 220μA
Vgs (Max) $\pm 20 \text{V}$ FET FeatureSuper JunctionPower Dissipation (Max) 29W (Tc) Rds On (Max) @ Id, Vgs $450 \text{ mOhm } @ 4.5 \text{A}, 10 \text{V}$ Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C (TJ)}$ Mounting TypeThrough HoleSupplier Device PackageTO-220-3FPackage / CaseTO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	24nC @ 10V
FET Feature Super Junction Power Dissipation (Max) Rds On (Max) @ Id, Vgs 450 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Input Capacitance (Ciss) (Max) @ Vds	770pF @ 500V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 450 mOhm @ 4.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs450 mOhm @ 4.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220-3FPackage / CaseTO-220-3 Full Pack	FET Feature	Super Junction
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	29W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	450 mOhm @ 4.5A, 10V
Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220-3F
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

IPA80R450P7XKSA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPA80R450P7XKSA1 Payment Methods

































If you have any question about IPA80R450P7XKSA1, please do not hesitate to contact us!

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